Low-Voltage 1.8/2.5/3.3V 16-Bit Transceiver

With 3.6 V–Tolerant Inputs and Outputs (3–State, Non–Inverting)

The 74VCXH16245 is an advanced performance, non-inverting 16–bit transceiver. It is designed for very high–speed, very low–power operation in 1.8 V, 2.5 V or 3.3 V systems.

When operating at 2.5 V (or 1.8 V) the part is designed to tolerate voltages it may encounter on either inputs or outputs when interfacing to 3.3 V busses. It is guaranteed to be over-voltage tolerant to 3.6 V.

The VCXH16245 is designed with byte control. It can be operated as two separate octals, or with the controls tied together, as a 16-bit wide function. The Transmit/Receive (T/Rn) inputs determine the direction of data flow through the bi-directional transceiver. Transmit (active-HIGH) enables data from A ports to B ports; Receive (active-LOW) enables data from B to A ports. The Output Enable inputs (\overline{OEn}), when HIGH, disable both A and B ports by placing them in a HIGH Z condition. The data inputs include active bushold circuitry, eliminating the need for external pull-up resistors to hold unused or floating inputs at a valid logic state.

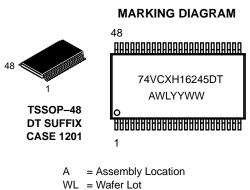
- Designed for Low Voltage Operation: $V_{CC} = 1.65-3.6$ V
- 3.6 V Tolerant Inputs and Outputs
- High Speed Operation: 2.5 ns max for 3.0 to 3.6 V 3.0 ns max for 2.3 to 2.7 V

6.0 ns max for 1.65 to 1.95 V

- Static Drive: ±24 mA Drive at 3.0 V ±18 mA Drive at 2.3 V ±6 mA Drive at 1.65 V
- Supports Live Insertion and Withdrawal
- Includes Active Bushold to Hold Unused or Floating Inputs at a Valid Logic State
- I_{OFF} Specification Guarantees High Impedance When $V_{CC} = 0 V^{\dagger}$
- Near Zero Static Supply Current in All Three Logic States (20 μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds ±300 mA @ 125°C
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



http://onsemi.com



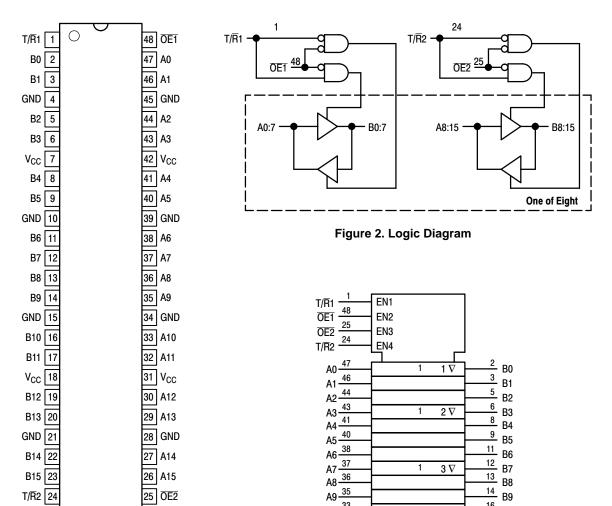
YY = Year

WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
74VCXH16245DT	TSSOP	39 / Rail
74VCXH16245DTR	TSSOP	2500 / Reel

[†]NOTE: To ensure the outputs activate in the 3–state condition, the output enable pins should be connected to V_{CC} through a pull–up resistor. The value of the resistor is determined by the current sinking capability of the output connected to the \overline{OE} pin.



A10 33

A11 32

A11 <u>30</u> A12 <u>30</u> A13 <u>29</u>

A14 27

A15 26

B9

B12 20 B13

22 B14

23 B15

16 B10

17 B11

19

1

4 ∇

Figure 1. 48–Lead Pinout (Top View)

25 OE2

PIN NAMES

T/R2 24

Pins	Function
OEn	Output Enable Inputs
T/Rn	Transmit/Receive Inputs
A0-A15	Side A Inputs or 3–State Outputs
B0-B15	Side B Inputs or 3–State Outputs

Inp	uts	Outpute	Inp	uts	Outpute
OE1	T/R1	Outputs	OE2 T/R2		Outputs
L	L	Bus B0:7 Data to Bus A0:7	L	L	Bus B8:15 Data to Bus A8:15
L	Н	Bus A0:7 Data to Bus B0:7	L	Н	Bus A8:15 Data to Bus B8:15
Н	Х	High Z State on A0:7, B0:7	Н	Х	High Z State on A8:15, B8:15

H = High Voltage Level; L = Low Voltage Level; X = High or Low Voltage Level and Transitions Are Acceptable

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +4.6		V
VI	DC Input Voltage	$-0.5 \le V_1 \le +4.6$		V
Vo	DC Output Voltage	$-0.5 \le V_{O} \le +4.6$	Output in 3–State	V
		$-0.5 \le V_O \le V_{CC} + 0.5$	Note 1.; Outputs Active	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{OK}	DC Output Diode Current	-50	V _O < GND	mA
		+50	$V_{O} > V_{CC}$	mA
I _O	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage	Operating Data Retention Only	1.65 1.2	3.3 3.3	3.6 3.6	V
VI	Input Voltage		-0.3		3.6	V
V _O	Output Voltage	(Active State) (3–State)	0 0		V _{CC} 3.6	V
I _{OH}	HIGH Level Output Current, V _{CC} = 3.0V - 3.6V				-24	mA
I _{OL}	LOW Level Output Current, $V_{CC} = 3.0V - 3.6V$				24	mA
I _{OH}	HIGH Level Output Current, $V_{CC} = 2.3V - 2.7V$				-18	mA
I _{OL}	LOW Level Output Current, V _{CC} = 2.3V – 2.7V				18	mA
I _{OH}	HIGH Level Output Current, V _{CC} = 1.65 – 1.95V				-6	mA
I _{OL}	LOW Level Output Current, V_{CC} = 1.65 – 1.95V				6	mA
T _A	Operating Free–Air Temperature		-40		+85	°C
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate, VIN from 0.8V to	2.0V, V _{CC} = 3.0V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = -40°	C to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
V _{IH}	HIGH Level Input Voltage (Note 2.)	$1.65V \le V_{CC} < 2.3V$	0.65 x V _{CC}		V
		$2.3V \le V_{CC} \le 2.7V$	1.6		
		$2.7V < V_{CC} \le 3.6V$	2.0		
V _{IL}	LOW Level Input Voltage (Note 2.)	$1.65V \le V_{CC} < 2.3V$		0.35 x V _{CC}	V
		$2.3V \le V_{CC} \le 2.7V$		0.7	
		$2.7V < V_{CC} \le 3.6V$		0.8	
V _{OH}	HIGH Level Output Voltage	$1.65V \le V_{CC} \le 3.6V; I_{OH} = -100\mu A$	V _{CC} – 0.2		V
		V _{CC} = 1.65V; I _{OH} = -6mA	1.25		
		V _{CC} = 2.3V; I _{OH} = -6mA	2.0		
		V _{CC} = 2.3V; I _{OH} = -12mA	1.8		
		V _{CC} = 2.3V; I _{OH} = -18mA	1.7		
		$V_{CC} = 2.7V; I_{OH} = -12mA$	2.2		
		V _{CC} = 3.0V; I _{OH} = -18mA	2.4		
		V _{CC} = 3.0V; I _{OH} = -24mA	2.2		
V _{OL}	LOW Level Output Voltage	$1.65V \le V_{CC} \le 3.6V; \ I_{OL} = 100 \mu A$		0.2	V
		V _{CC} = 1.65V; I _{OL} = 6mA		0.3	
		V _{CC} = 2.3V; I _{OL} = 12mA		0.4	
		V _{CC} = 2.3V; I _{OL} = 18mA		0.6	
		V _{CC} = 2.7V; I _{OL} = 12mA		0.4	
	V _{CC} = 3.0V; I _{OL} = 18mA		0.4		
		V _{CC} = 3.0V; I _{OL} = 24mA		0.55	
lı	Input Leakage Current	$1.65V \le V_{CC} \le 3.6V; \ 0V \le V_I \le 3.6V$		±5.0	μA
I _{I(HOLD)}	Minimum Bushold Input Current	V _{CC} = 3.0V, V _{IN} = 0.8V	75		μA
		V _{CC} = 3.0V, V _{IN} = 2.0V	-75		
		$V_{CC} = 2.3 V, V_{IN} = 0.7 V$	45		
		V _{CC} = 2.3V, V _{IN} = 1.6V	-45		
		V _{CC} = 1.65V, V _{IN} = 0.57V	25		
		V _{CC} = 1.65V, V _{IN} = 1.07V	-25		
I _{I (OD)}	Minimum Bushold Over–Drive	V _{CC} = 3.6V, (Note 3.)	450		μA
	Current Needed to Change State	V _{CC} = 3.6V, (Note 4.)	-450		
		V _{CC} = 2.7V, (Note 3.)	300		
		V _{CC} = 2.7V, (Note 4.)	-300		
		V _{CC} = 1.95V, (Note 3.)	200		
		V _{CC} = 1.95V, (Note 4.)	-200		
l _{oz}	3-State Output Current	$1.65V \leq V_{CC} \leq 3.6V; \ 0V \leq V_O \leq 3.6V; \\ V_I = V_{IH} \ or \ V_{IL}$		±10	μA
I _{OFF}	Power–Off Leakage Current	V_{CC} = 0V; V_{I} or V_{O} = 3.6V	1	10	μA
I _{CC}	Quiescent Supply Current (Note 5.)	$1.65V \le V_{CC} \le 3.6V$; V _I = GND or V _{CC}	1	20	μA
		$1.65V \le V_{CC} \le 3.6V; \ 3.6V \le V_I, \ V_O \le 3.6V$	1	±20	μA
Δl _{CC}	Increase in I _{CC} per Input	$2.7V < V_{CC} \le 3.6V; V_{IH} = V_{CC} - 0.6V$	1	750	μA

These values of V_I are used to test DC electrical characteristics only.
An external driver must source at least the specified current to switch from LOW-to-HIGH
An external driver must source at least the specified current to switch from HIGH-to-LOW
Outputs disabled or 3-state only.

AC CHARACTERISTICS (Note 6.; $t_R = t_F = 2.0ns$; $C_L = 30pF$; $R_L = 500\Omega$)

					Lir	nits			
					T _A = -40°	C to +85°C			
			V _{CC} = 3.0	0V to 3.6V	V _{CC} = 2.3	3V to 2.7V	$V_{CC} = 1.0$	65 to1.95V	
Symbol	Parameter	Waveform	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output	1	0.8 0.8	2.5 2.5	1.0 1.0	3.0 3.0	1.5 1.5	6.0 6.0	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	2	0.8 0.8	3.8 3.8	1.0 1.0	4.9 4.9	1.5 1.5	9.3 9.3	ns
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	2	0.8 0.8	3.7 3.7	1.0 1.0	4.2 4.2	1.5 1.5	7.6 7.6	ns
t _{OSHL} t _{OSLH}	Output-to-Output Skew (Note 7.)			0.5 0.5		0.5 0.5		0.75 0.75	ns

6. For $C_L = 50$ pF, add approximately 300 ps to the AC maximum specification.

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

DYNAMIC SWITCHING CHARACTERISTICS

			T _A = +25°C	
Symbol	Characteristic	Condition	Тур	Unit
V _{OLP}	Dynamic LOW Peak Voltage	$V_{CC} = 1.8V, \ C_L = 30 p F, \ V_{IH} = V_{CC}, \ V_{IL} = 0 V$	0.25	V
	(Note 8.)	$V_{CC} = 2.5 \text{V}, \text{C}_{\text{L}} = 30 \text{pF}, \text{V}_{\text{IH}} = \text{V}_{CC}, \text{V}_{\text{IL}} = 0 \text{V}$	0.6	
		V_{CC} = 3.3V, C_L = 30pF, V_{IH} = $V_{CC}, \ V_{IL}$ = 0V	0.8	
V _{OLV}	Dynamic LOW Valley Voltage	$V_{CC} = 1.8 \text{V}, \text{C}_{\text{L}} = 30 \text{pF}, \text{V}_{\text{IH}} = \text{V}_{CC}, \text{V}_{\text{IL}} = 0 \text{V}$	-0.25	V
	(Note 8.)	$V_{CC} = 2.5 \text{V}, \text{C}_{\text{L}} = 30 \text{pF}, \text{V}_{\text{IH}} = \text{V}_{CC}, \text{V}_{\text{IL}} = 0 \text{V}$	-0.6	
		$V_{CC}=3.3 \text{V}, \text{C}_{\text{L}}=30 \text{p}\text{F}, \text{V}_{\text{IH}}=\text{V}_{CC}, \text{V}_{\text{IL}}=0 \text{V}$	-0.8	
V _{OHV}	Dynamic HIGH Valley Voltage	$V_{CC} = 1.8 \text{V}, \text{C}_{\text{L}} = 30 \text{pF}, \text{V}_{\text{IH}} = \text{V}_{CC}, \text{V}_{\text{IL}} = 0 \text{V}$	1.5	V
	(Note 9.)	$V_{CC} = 2.5 \text{V}, \text{C}_{\text{L}} = 30 \text{p}\text{F}, \text{V}_{\text{IH}} = \text{V}_{CC}, \text{V}_{\text{IL}} = 0 \text{V}$	1.9	
		$V_{CC} = 3.3 \text{V}, \text{C}_{\text{L}} = 30 \text{pF}, \text{V}_{\text{IH}} = \text{V}_{CC}, \text{V}_{\text{IL}} = 0 \text{V}$	2.2	

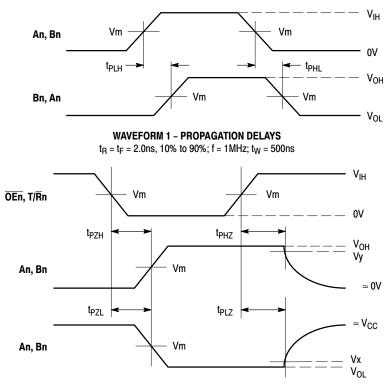
 Number of outputs defined as "n". Measured with "n–1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

9. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the HIGH state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	Note 10.	6	pF
C _{OUT}	Output Capacitance	Note 10.	7	pF
C _{PD}	Power Dissipation Capacitance	Note 10., 10MHz	20	pF

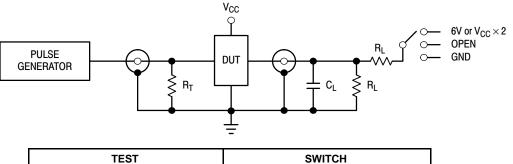
10. V_{CC} = 1.8, 2.5 or 3.3V; V_{I} = 0V or V_{CC} .



WAVEFORM 2 - OUTPUT ENABLE AND DISABLE TIMES $t_{R} = t_{F} = 2.0$ ns, 10% to 90%; f = 1MHz; $t_{W} = 500$ ns

Figure 3. AC Waveforms

	V _{CC}				
Symbol	3.3V ±0.3V	2.5V ±0.2V	1.8V ±0.15V		
V _{IH}	2.7V	V _{CC}	V _{CC}		
Vm	1.5V	V _{CC} /2	V _{CC} /2		
V _x	V _{OL} + 0.3V	V _{OL} + 0.15V	V _{OL} + 0.15V		
Vy	V _{OH} – 0.3V	V _{OH} – 0.15V	V _{OH} – 0.15V		

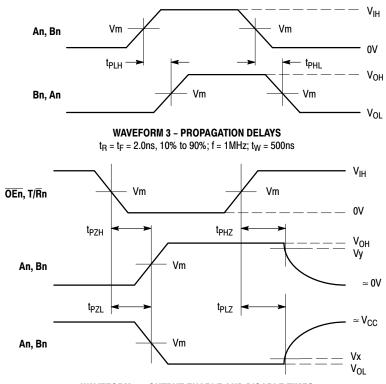


TEST	SWITCH
t _{PLH} , t _{PHL}	Open
t _{PZL} , t _{PLZ}	6V at V _{CC} = 3.3 ±0.3V; V _{CC} × 2 at V _{CC} = 2.5 ±0.2V; 1.8V ±0.15V
t _{PZH} , t _{PHZ}	GND

C_L = 30pF or equivalent (Includes jig and probe capacitance)

 $R_L = 500\Omega$ or equivalent $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

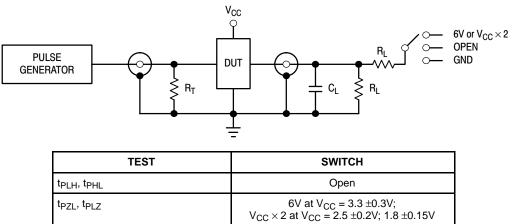
Figure 4. Test Circuit



WAVEFORM 4 – OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.0ns, 10\%$ to 90%; f = 1MHz; $t_W = 500ns$

Figure 5. AC Waveforms

	V _{CC}		
Symbol	3.3V ±0.3V	2.7V	
V _{IH}	2.7V	2.7V	
V _m	1.5V	1.5V	
V _x	V _{OL} + 0.3V	V _{OL} + 0.3V	
Vy	V _{OH} – 0.3V	V _{OH} – 0.3V	



 $C_L = 50 pF$ or equivalent (Includes jig and probe capacitance)

GND

 $R_L = 500\Omega$ or equivalent

t_{PZH}, t_{PHZ}

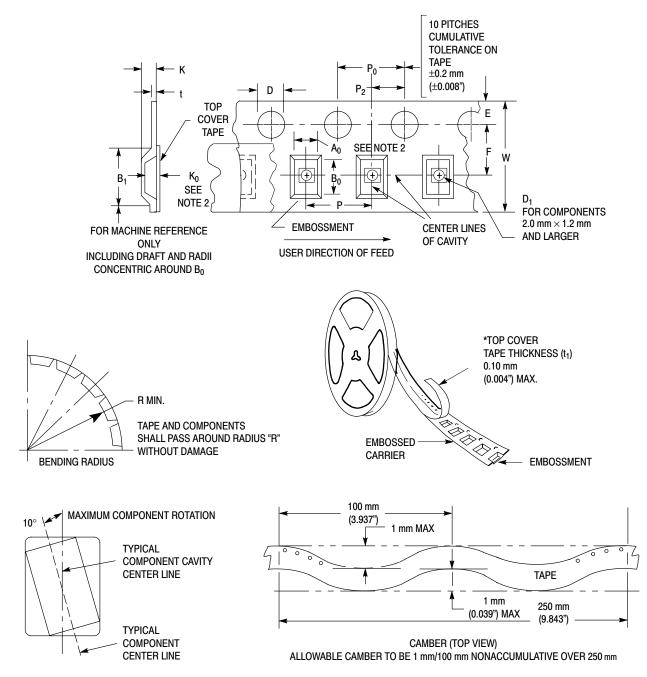
 $R_T = Z_{OUT}$ of pulse generator (typically 50 Ω)

Figure 6. Test Circuit

AC CHARACTERISTICS ($t_R = t_F = 2.0ns$; $C_L = 50pF$; $R_L = 500\Omega$)

			Limits T _A = -40°C to +85°C				-
			V _{CC} = 3.0V to 3.6V		V _{CC} = 2.7V		
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit
t _{PLH} t _{PHL}	Propagation Delay Input to Output	3	1.0 1.0	3.0 3.0		3.6 3.6	ns
t _{PZH} t _{PZL}	Output Enable Time to High and Low Level	4	1.0 1.0	4.4 4.4		5.4 5.4	ns
t _{PHZ} t _{PLZ}	Output Disable Time From High and Low Level	4	1.0 1.0	4.1 4.1		4.6 4.6	ns
t _{OSHL} t _{OSLH}	Output–to–Output Skew (Note 11.)			0.5 0.5		0.5 0.5	ns

11. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.





Tape Size	B ₁ Max	D	D ₁	E	F	к	Р	P ₀	P ₂	R	т	w
24mm	20.1mm (0.791")	1.5 + 0.1mm -0.0 (0.059 +0.004" -0.0)	1.5mm Min (0.060")	1.75 ±0.1 mm (0.069 ±0.004")	11.5 ±0.10 mm (0.453 ±0.004")	11.9 mm Max (0.468")	16.0 ±0.1 mm (0.63 ±0.004")	4.0 ±0.1 mm (0.157 ±0.004")	2.0 ±0.1 mm (0.079 ±0.004")	30 mm (1.18")	0.6 mm (0.024")	24.3 mm (0.957")

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

1. Metric Dimensions Govern-English are in parentheses for reference only.

 A₀, B₀, and K₀ are determined by component size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

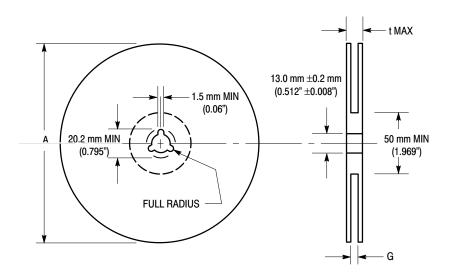
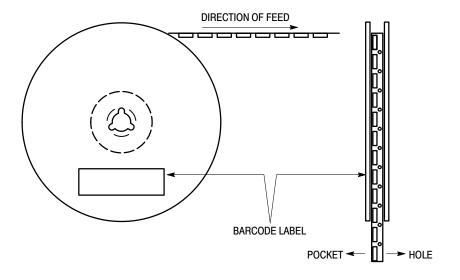


Figure 8. Reel Dimensions

REEL DIMENSIONS

Tape Size	A Max	G	t Max
24 mm	360 mm	24.4 mm + 2.0 mm, -0.0	30.4 mm
	(14.173")	(0.961" + 0.078", -0.00)	(1.197")





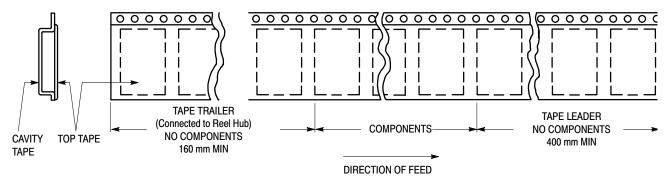
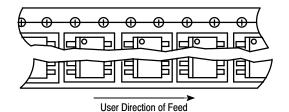
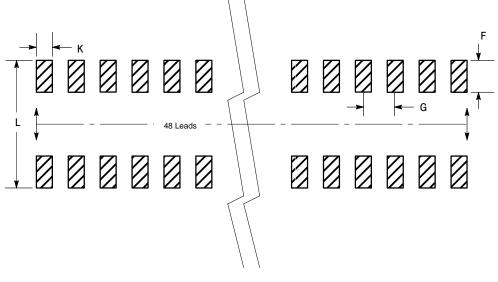


Figure 10. Tape Ends for Finished Goods



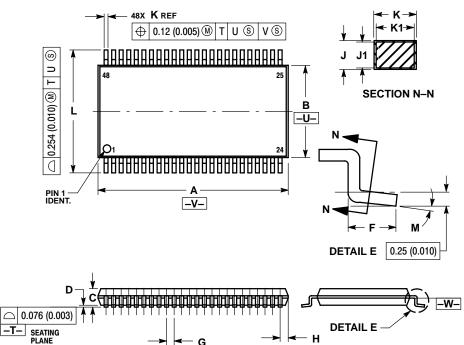




Package Footprint

PACKAGE DIMENSIONS

TSSOP DT SUFFIX CASE 1201-01 ISSUE A



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS
- SHALL NOT EXCEED 0.15 (0.006) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR 4
- PROTRUSION R DOES NOT INCLODE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY. DIMENSIONS A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	12.40	12.60	0.488	0.496	
В	6.00	6.20	0.236	0.244	
C		1.10		0.043	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.50	BSC	0.0197 BSC		
н	0.37		0.015		
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.17	0.27	0.007	0.011	
K1	0.17	0.23	0.007	0.009	
L	7.95	8.25	0.313	0.325	
М	0 °	8 °	0 °	8 °	

are trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes ON Semiconductor and without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights or the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

NORTH AMERICA Literature Fulfillment:

 \cap

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: ONlit@hibbertco.com Fax Response Line: 303-675-2167 or 800-344-3810 Toll Free USA/Canada

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

- EUROPE: LDC for ON Semiconductor European Support German Phone: (+1) 303-308-7140 (Mon-Fri 2:30pm to 7:00pm CET)
- Email: ONlit-german@hibbertco.com Phone: (+1) 303-308-7141 (Mon-Fri 2:00pm to 7:00pm CET) French
- Email: ONlit-french@hibbertco.com English Phone: (+1) 303-308-7142 (Mon-Fri 12:00pm to 5:00pm GMT)
- Email: ONlit@hibbertco.com

EUROPEAN TOLL-FREE ACCESS*: 00-800-4422-3781 *Available from Germany, France, Italy, UK

CENTRAL/SOUTH AMERICA:

Spanish Phone: 303-308-7143 (Mon-Fri 8:00am to 5:00pm MST) Email: ONlit-spanish@hibbertco.com

ASIA/PACIFIC: LDC for ON Semiconductor - Asia Support Phone: 303-675-2121 (Tue-Fri 9:00am to 1:00pm, Hong Kong Time) Toll Free from Hong Kong & Singapore: 001-800-4422-3781 Email: ONlit-asia@hibbertco.com

JAPAN: ON Semiconductor, Japan Customer Focus Center 4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031 Phone: 81-3-5740-2745 Email: r14525@onsemi.com

ON Semiconductor Website: http://onsemi.com

For additional information, please contact your local Sales Representative.